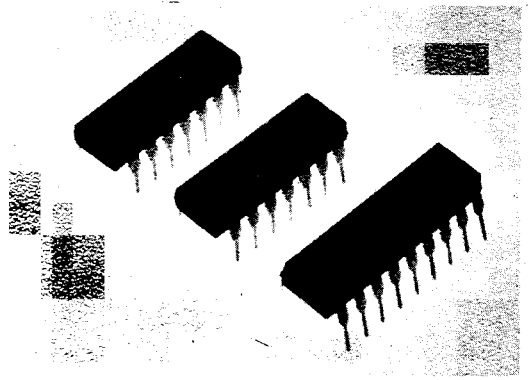
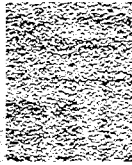


DIONICS INC.

65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-997-7474

HIGH VOLTAGE SILICON PNP TRANSISTOR ARRAYS



The Dionics DI 402P, DI 602P and DI 802P Series of High Voltage PNP Transistor arrays are specifically designed for plasma and gas discharge display driver applications:

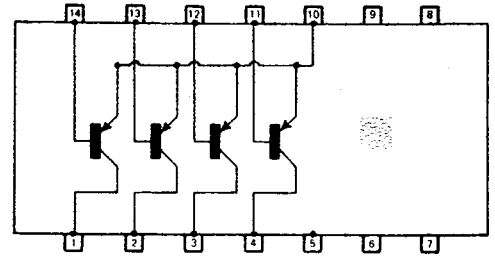
A unique process technology* permits the use of high voltage while still maintaining NANO-AMP level leakage currents. The arrays are groups of four, six or eight PNP high voltage transistors, connected in the common emitter configuration. The DI 602P and DI 802P Series have split emitter Buss Bar connections to allow multiplexing between display anodes.

* Pat. Pend.

ABSOLUTE MAXIMUM RATINGS @ 25°C. AMBIENT

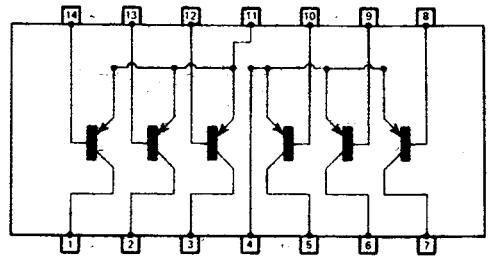
	DI 402P DI 602P DI 802P	DI 403P DI 603P DI 803P	DI 404P DI 604P DI 804P	DI 405P DI 605P DI 805P
COLLECTOR-BASE VOLTAGE	150V	125V	100V	75V
COLLECTOR-EMITTER VOLTAGE	150V	125V	100V	75V
EMITTER-BASE VOLTAGE	5.0V	5.0V	5.0V	5.0V
D.C. COLLECTOR CURRENT	20 MA	20 MA	20 MA	20 MA
POWER DISSIPATION PER TRANSISTOR	360 MW	360 MW	360 MW	360 MW
STORAGE TEMP RANGE ..	←————— -65 to +150°C —————→			
OPERATING TEMP RANGE ..	←————— -55 to +70°C —————→			

DI 402P



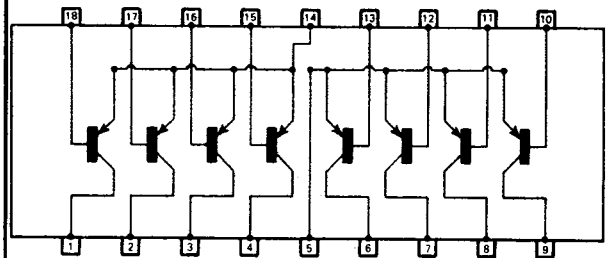
4 DIGIT ANODE DRIVER

DI 602P

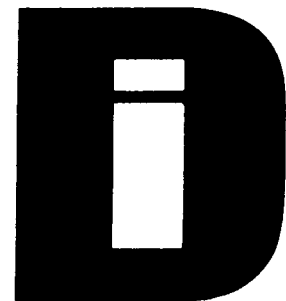


6 DIGIT ANODE DRIVER

DI 802P



8 DIGIT ANODE DRIVER

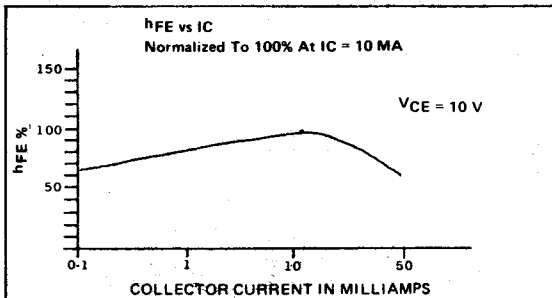


The Dionics Driver Arrays greatly increase reliability, while reducing the large number of discrete high voltage transistors normally used in this application, with an associated reduction of insertion costs and circuit board space requirements.

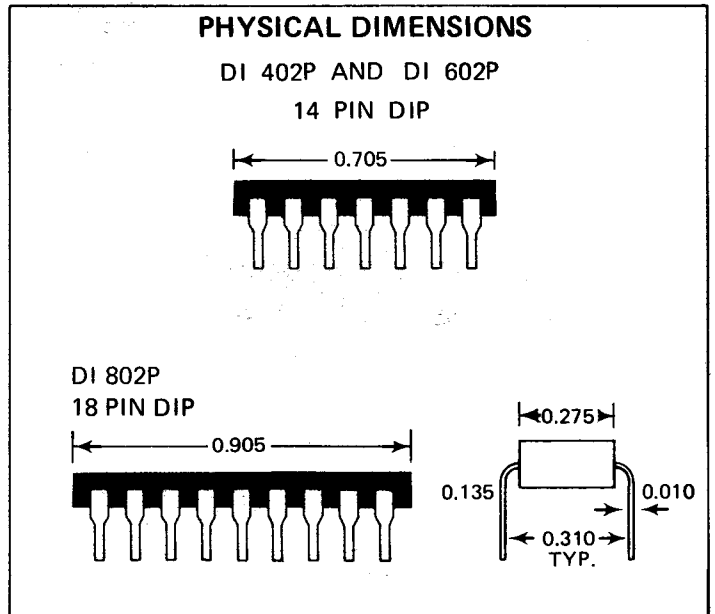
CHARACTERISTICS AT 25°C CASE TEMPERATURE (unless otherwise noted)

ELECTRICAL CHARACTERISTICS	TEST SYMBOL.	TEST CONDITIONS	DI 402P DI 602P DI 802P		DI 403P DI 603P DI 803P		DI 404P DI 604P DI 804P		DI 405P DI 605P DI 805P		UNITS
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
Collector Breakdown Voltage	BVCBO	IC= 10μA IE=0	150		125		100		75		Volts
Collector-Emitter, Breakdown Voltage	BVCEO	IC= 1 MA IB=0	150		125		100		75		Volts
Collector-Emitter, Breakdown Voltage	BVCE(sus)*	IC= 10 MA IB=0	150		125		100		75		Volts
Emitter Breakdown Voltage	BVEBO	IB= 10μA IC=0	5.0		5.0		5.0		5.0		Volts
D.C. Current Gain	hFE	IC= 10 MA VCE=10V	25		25		25		25		—
Base to Emitter Saturation Voltage	VBE(Sat)	IC= 10 MA IB= 1 MA		1.2		1.2		1.2		1.2	Volts
Collector to Base Cut off Current	ICBO	VCBO= 125V IE=0		0.5		—		—		—	μA
		100V		—		0.5		—		—	μA
		75V		—		—		0.5		—	μA
		50V		—		—		—		0.5	μA
A.C. Current Gain	hFE	IC= 10 MA VCE= 10V f= 100MHZ	0.5		0.5		0.5		0.5		Typical
Common Base Output Capacitance	cob	VCB= 10V IE=0		8.0		8.0		8.0		8.0	pF

* Pulse Test: Pulse Width=300μS Duty Cycle=2%



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